

ABSTRACT OF THE DISCLOSURE

A nonvolatile semiconductor memory device having MONOS type memory cells of increased efficiency by hot electron injection and improved scaling characteristics includes a channel forming region in the vicinity of a surface of a substrate, first and second impurity regions, acting as a source and a drain in operation, formed in the vicinity of the surface of the substrate sandwiching the channel forming region between them, a gate insulating film stacked on the channel forming region and having a plurality of films, and a charge storing means that is formed in the gate insulating film dispersed in the plane facing the channel forming region. A bottom insulating film includes a dielectric film that exhibits a FN type electroconductivity and makes the energy barrier between the bottom insulating film and the substrate lower than that between silicon dioxide and silicon.